

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI HF8-28S** is Designed for

**FEATURES:**

- $P_G = 21$  dB min. at 8 W/30 MHz
- $IMD_3 = -30$  dBc max. at 8 W<sub>(PEP)</sub>
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	1.0 A
$V_{CBO}$	65 V
$V_{CEO}$	35 V
$V_{CES}$	65 V
$V_{EBO}$	4.0 V
$P_{DISS}$	13.0 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$q_{JC}$	13.5 $^\circ C/W$

**PACKAGE STYLE .380 4L STUD**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

**ORDER CODE: ASI10601**

**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 200$ mA	65			V
$BV_{CES}$	$I_C = 200$ mA	65			V
$BV_{CEO}$	$I_C = 200$ mA	35			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CBO}$	$V_{CB} = 30$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 200$ mA	5.0		---	---
$C_{OB}$	$V_{CB} = 30$ V $f = 1.0$ MHz			15	pF
$G_p$	$V_{CC} = 28$ V $P_{IN} = 1.0$ W $f = 150$ MHz	10			dB